High-Current, High & Low-Side, Gate-Drive IC

FAN7390

Description

The FAN7390 is a monolithic high- and low-side gate-drive IC, which can drive high speed MOSFETs and IGBTs that operate up to +600 V. It has a buffered output stage with all NMOS transistors designed for high pulse current driving capability and minimum cross-conduction.

ON Semiconductor's high-voltage process and common-mode noise canceling techniques provide stable operation of the high-side driver under high dv/dt noise circumstances. An advanced level shift circuit offers high-side gate driver operation up to $V_S = -9.8~V$ (typical) for $V_{BS} = 15~V$.

The UVLO circuit prevents malfunction when V_{DD} and V_{BS} are lower than the specified threshold voltage.

The high current and low output voltage drop feature make this device suitable for the PDP sustain pulse driver, motor driver, switching power supply, and high- power DC-DC converter applications.

Features

- Floating Channels for Bootstrap Operation to +600 V
- Typically 4.5 A / 4.5 A Sourcing / Sinking Current Driving Capability
- Common-Mode dv/dt Noise-Canceling Circuit
- Built-in Under-Voltage Lockout for Both Channels
- Matched Propagation Delay for Both Channels
- Logic (V_{SS}) and Power (COM) Ground ±7 V Offset
- 3.3 V and 5 V Input Logic Compatible
- Output In-Phase with Input
- This is a Pb-Free Device

Applications

- PDP Sustain Driver
- HID Lamp Ballast
- SMPS
- Motor Driver



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SOIC8 8-SOP CASE 751EG SOIC14 14-SOP CASE 751ER

MARKING DIAGRAM





FAN7390MX

FAN7390M1X

7390, = Device Code

FAN7390

A = Assembly Site
L = Wafer Lot Number
YW = Assembly Start Week
&Z = Assembly Plant Code
&3 = 3-Digit Date Code

&K = 2-Digits Lot Run Traceability Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 12 of this data sheet.

TYPICAL APPLICATION CIRCUIT

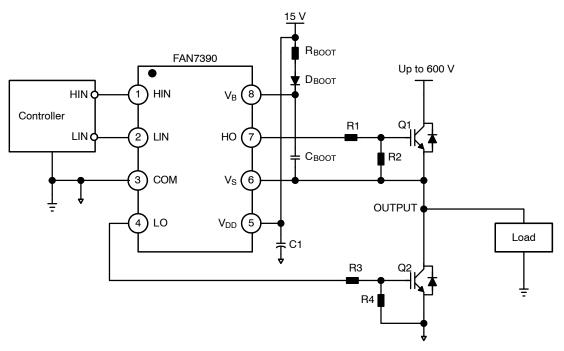


Figure 1. Application Circuit for Half-Bridge (Referenced 8-SOP)

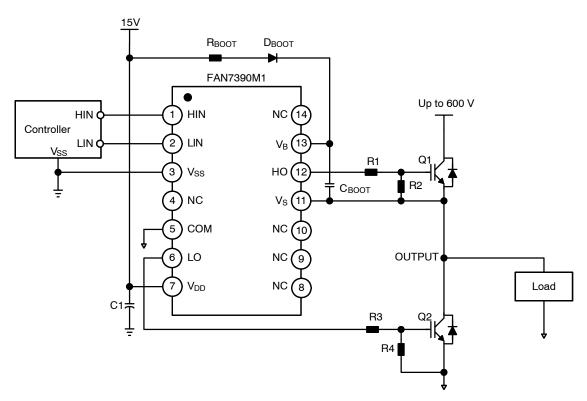


Figure 2. Application Circuit for Half-Bridge (Referenced 14-SOP)

INTERNAL BLOCK DIAGRAM

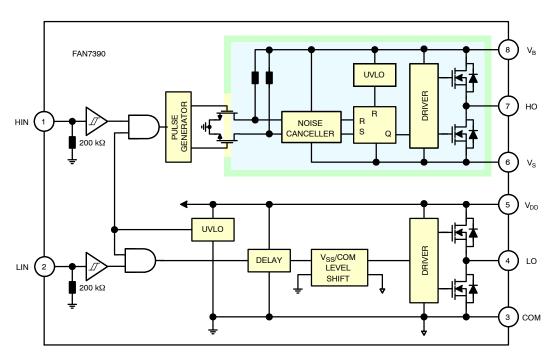


Figure 3. Functional Block Diagram (Referenced 8-SOP)

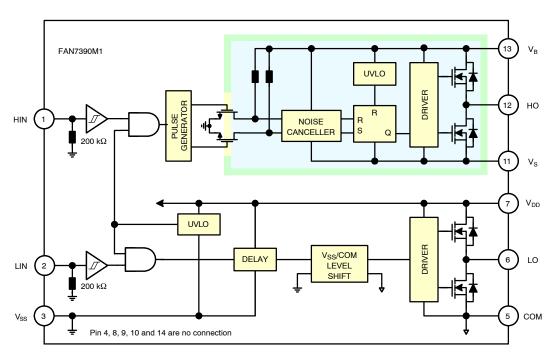


Figure 4. Functional Block Diagram (Referenced 14-SOP)

PIN CONFIGURATION

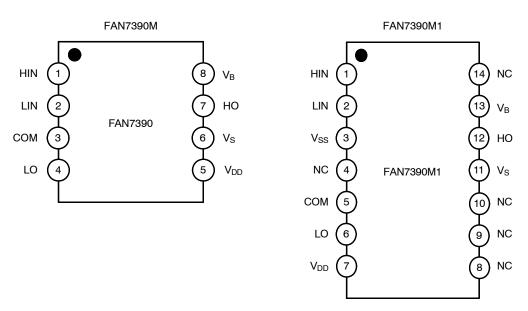


Figure 5. Pin Assignments (Top View)

PIN DEFINITIONS

8–Pin	14-Pin	Name	Description
1	1	HIN	Logic Input for High-Side Gate Driver Output
2	2	LIN	Logic Input for Low-Side Gate Driver Output
	3	V _{SS}	Logic Ground (FAN7390M1 only)
3	5	СОМ	Low-Side Driver Return
4	6	LO	Low-Side Driver Output
5	7	V_{DD}	Low-Side and Logic Part Supply Voltage
6	11	Vs	High-Voltage Floating Supply Return
7	12	НО	High-Side Driver Output
8	13	V _B	High-Side Floating Supply
	4, 8, 9, 10, 14	NC	No Connect

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$, unless otherwise noted)

Symbol	Characteristics	Min	Max	Unit
V _S	High-Side Floating Supply Offset Voltage	V _B – 25	V _B + 0.3	V
V _B	High-Side Floating Supply Voltage	-0.3	625.0	V
V_{HO}	High-Side Floating Output Voltage HO	V _S - 0.3	V _B + 0.3	V
V_{DD}	Low-Side and Logic Fixed Supply Voltage	-0.3	25.0	V
V_{LO}	Low-Side Output Voltage LO	-0.3	V _{DD} + 0.3	V
V _{IN}	Logic Input Voltage (HIN and LIN)	V _{SS} - 0.3	V _{DD} + 0.3	V
V_{SS}	Logic Ground (FAN7390M1 only)	V _{DD} – 25	V _{DD} + 0.3	V
dV _S /dt	Allowable Offset Voltage Slew Rate	-	50	V/ns
P _D	Power Dissipation	8-SOP	0.625	W
(Note 1, 2, 3)		14-SOP	1.000	
$\theta_{\sf JA}$	Thermal Resistance, Junction-to-Ambient	8-SOP	200	°C/W
		14-SOP	110	
T_J	Junction Temperature	-	+150	°C
T _{STG}	Storage Temperature	-	+150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Mounted on 76.2 x 114.3 x 1.6 mm PCB (FR-4 glass epoxy material).

- Refer to the following standards: JESD51–2: Integral circuits thermal test method environmental conditions natural convection JESD51-3: Low effective thermal conductivity test board for leaded surface mount packages.
- 3. Do not exceed $P_{\mbox{\scriptsize D}}$ under any circumstances.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _B	High-Side Floating Supply Voltage	V _S + 10	V _S + 22	V
V _S	High-Side Floating Supply Offset Voltage	6 – V _{DD}	600	V
V _{HO}	High-Side Output Voltage	V _S	V _B	V
V_{DD}	Low-Side and Logic Supply Voltage	10	22	V
V _{LO}	Low-Side Output Voltage	СОМ	V_{DD}	V
V _{IN}	Logic Input Voltage (HIN and LIN)	V _{SS}	V_{DD}	V
T _A	Operating Ambient Temperature	-40	+125	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

ELECTRICAL CHARACTERISTICS (V_{BIAS} (V_{DD} , V_{BS}) = 15.0 V, $V_S = V_{SS} = COM$, $T_A = 25^{\circ}C$, unless otherwise specified. The V_{IL} , V_{IH} , and I_{IN} parameters are referenced to V_{SS}/COM and are applicable to the respective input signals HIN and LIN. The V_O and I_O parameters are referenced to COM and V_S is applicable to the respective output signals HO and LO.)

Symbol	Characteristics	Test Condition	Min	Тур	Max	Unit
POWER SU	PPLY SECTION (V _{DD} AND V _{BS})		•			
V _{DDUV+} V _{BSUV+}	V _{DD} and V _{BS} Supply Under-Voltage Positive-going Threshold		8.0	8.8	9.8	V
V _{DDUV} - V _{BSUV} -	V _{DD} and V _{BS} Supply Under-Voltage Negative-going Threshold		7.4	8.3	9.0	
V _{DDUVH} V _{BSUVH}	V _{DD} and V _{BS} Supply Under-Voltage Lockout Hysteresis Voltage		-	0.5	-	
I _{LK}	Offset Supply Leakage Current	V _B = V _S = 600 V	-	_	50	μΑ
I _{QBS}	Quiescent V _{BS} Supply Current	V _{IN} = 0 V or 5 V	-	45	80	
I _{QDD}	Quiescent V _{DD} Supply Current	V _{IN} = 0 V or 5 V	-	75	110	
I _{PBS}	Operating V _{BS} Supply Current	f _{IN} = 20 kHz, rms value	-	530	640	μΑ
I _{PDD}	Operating V _{DD} Supply Current	f _{IN} = 20 kHz, rms value	-	530	640	
OGIC INP	JT SECTION (HIN, LIN)					
V _{IH}	Logic "1" Input Voltage		2.5	-	-	V
V _{IL}	Logic "0" Input Voltage		-	-	1.2	
I _{IN+}	Logic "1" Input Bias Current	V _{IN} = 5 V	-	25	50	μΑ
I _{IN} _	Logic "0" Input Bias Current	V _{IN} = 0 V	-	1.0	2.0	
R _{IN}	Input Pull-down Resistance		100	200	-	kΩ
ATE DRIV	ER OUTPUT SECTION (HO, LO)					
V _{OH}	High-level Output Voltage, V _{BIAS} -V _O	No Load	-	-	1.0	V
V _{OL}	Low-level Output Voltage, V _O	No Load	1 -	-	35	mV
I _{O+}	Output High, Short-circuit Pulsed Current (Note 4)	$V_O = 0$ V, $V_{IN} = 5$ V with PW < 1 0 μ s	3.5	4.5		Α
I _O _	Output Low, Short-circuit Pulsed Current (Note 4)	$V_O = 15$ V, $V_{IN} = 0$ V with PW < 10 μ s	3.5	4.5	-	
V _S	Allowable Negative V _S Pin Voltage for HIN Signal Propagation to HO		-	-9.8	-7.0	V
V _{SS} -COM	V _{SS} -COM/COM-V _{SS} Voltage Endurability		-7.0	-	7.0	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

DYNAMIC ELECTRICAL CHARACTERISTICS (V_{BIAS} (V_{DD} , V_{BS}) = 15.0 V, V_{S} = V_{SS} = COM = 0 V, C_{L} = 1000 pF, and T_{A} = 25°C unless otherwise specified.)

Symbol	Characteristics	Test Condition	Min	Тур	Max	Unit
t _{on}	Turn-on Propagation Delay	V _S = 0 V	-	140	220	ns
t _{off}	Turn-off Propagation Delay	V _S = 0 V	-	140	220	
MT	Delay Matching, HS & LS Turn-on/off		-	0	50	
t _r	Turn-on Rise Time		-	25	50	
t _f	Turn-off Fall Time		-	20	45	

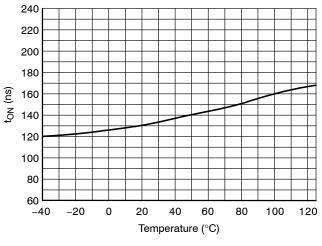
^{4.} This parameter guaranteed by design.

TYPICAL CHARACTERISTICS

240

220

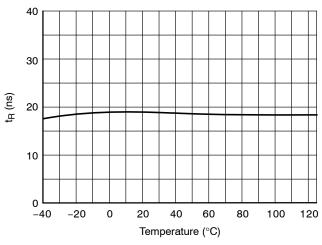
200



180 <u>ගි</u> 160 torr (140 120 100 80 60 60 -20 0 20 40 80 100 120 -40 Temperature (°C)

Figure 6. Turn-on Propagation Delay vs.
Temperature

Figure 7. Turn-off Propagation Delay vs.
Temperature



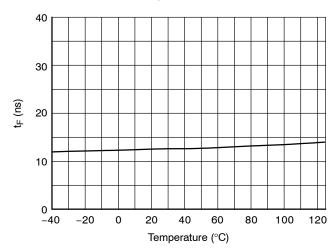
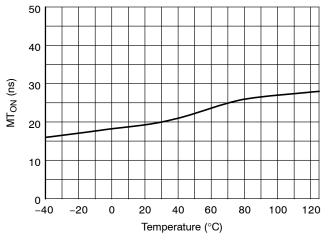


Figure 8. Turn-on Rise Time vs. Temperature

Figure 9. Turn-off Fall Time vs. Temperature



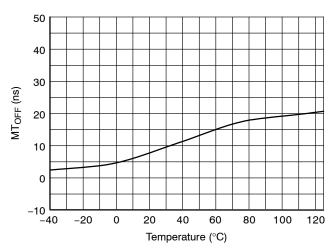
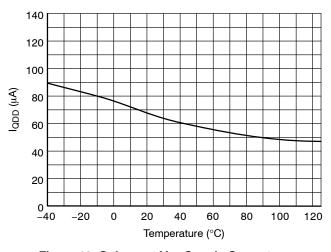


Figure 10. Turn-on Delay Matching vs. Temperature

Figure 11. Turn-off Delay Matching vs. Temperature

TYPICAL CHARACTERISTICS (continued)

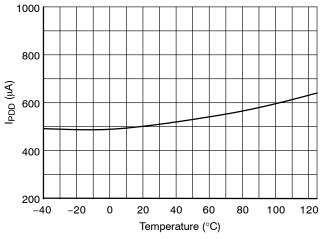
120



100 80 lges (µA) 60 40 20 0 40 60 -40 -20 0 20 80 100 120 Temperature (°C)

Figure 12. Quiescent V_{DD} Supply Current vs. Temperature

Figure 13. Quiescent V_{BS} Supply Current vs. Temperature



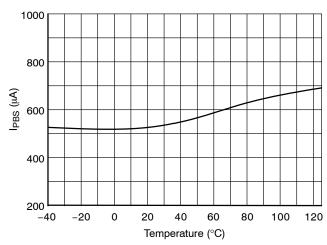
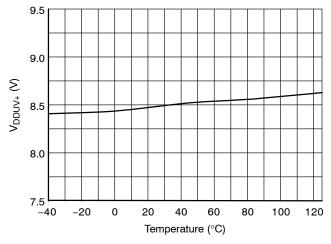


Figure 14. Operating V_{DD} Supply Current vs. Temperature

Figure 15. Operating V_{BS} Supply Current vs. Temperature



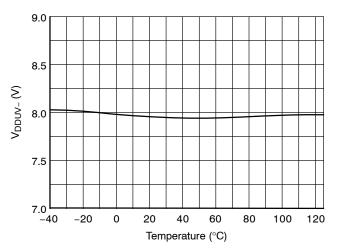


Figure 16. V_{DD} UVLO+ vs. Temperature

Figure 17. V_{DD} UVLO- vs. Temperature

TYPICAL CHARACTERISTICS (continued)

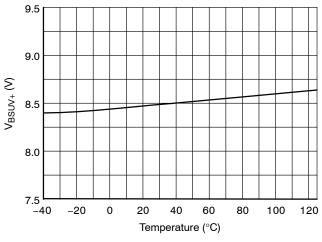


Figure 18. V_{BS} UVLO+ vs. Temperature

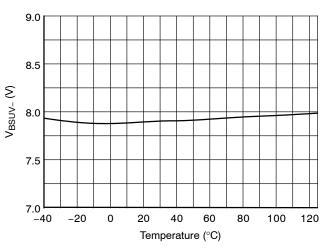


Figure 19. V_{BS} UVLO- vs. Temperature

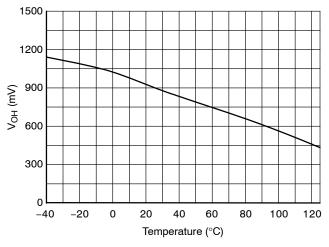


Figure 20. High-Level Output Voltage vs. Temperature

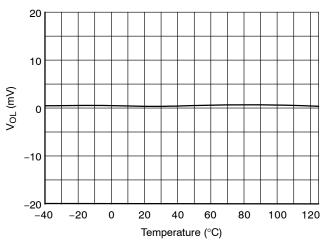


Figure 21. Low-Level Output Voltage vs. Temperature

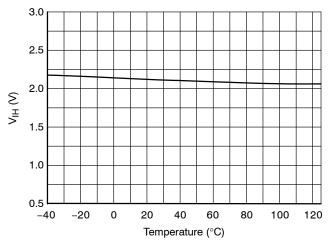


Figure 22. Logic High Input Voltage vs. Temperature

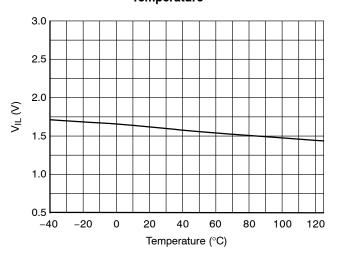
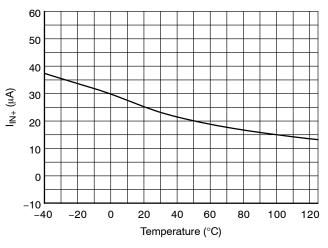


Figure 23. Low Input Voltage vs. Temperature

TYPICAL CHARACTERISTICS (continued)



-8
-9
-10
-11
-12
-40 -20 0 20 40 60 80 100 120
Temperature (°C)

Figure 24. Logic Input High Bias Current vs. Temperature

Figure 25. Allowable Negative V_{S} Voltage vs. Temperature

SWITCHING TIME DEFINITIONS

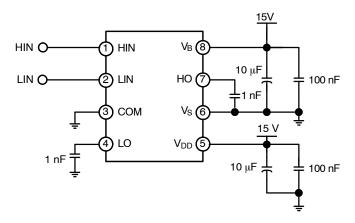


Figure 26. Switching Time Test Circuit (Referenced 8-SOP)

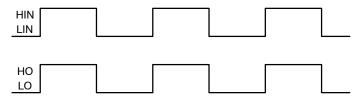


Figure 27. Input/Output Timing Diagram

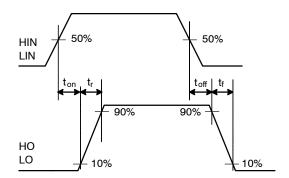


Figure 28. Switching Time Waveform Definitions

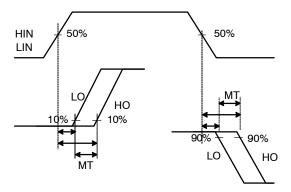


Figure 29. Delay Matching Waveform Definitions

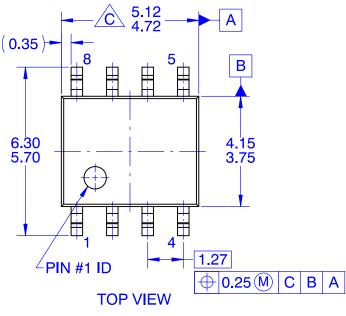
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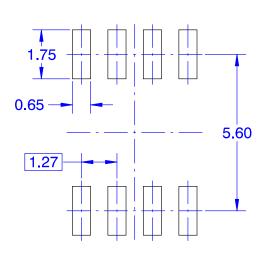
Device	Package	Operating Temperature Range	Shipping [†]
FAN7390MX	SOIC8 8-SOP (Pb-Free)	−40°C~125°C	3000 / Tape & Reel
FAN7390M1X	SOIC14 14-SOP (Pb-Free)		3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

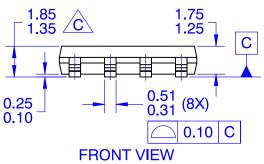
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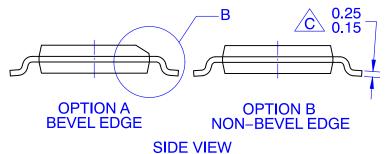
DATE 30 SEP 2016

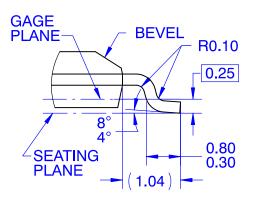




LAND PATTERN RECOMMENDATION







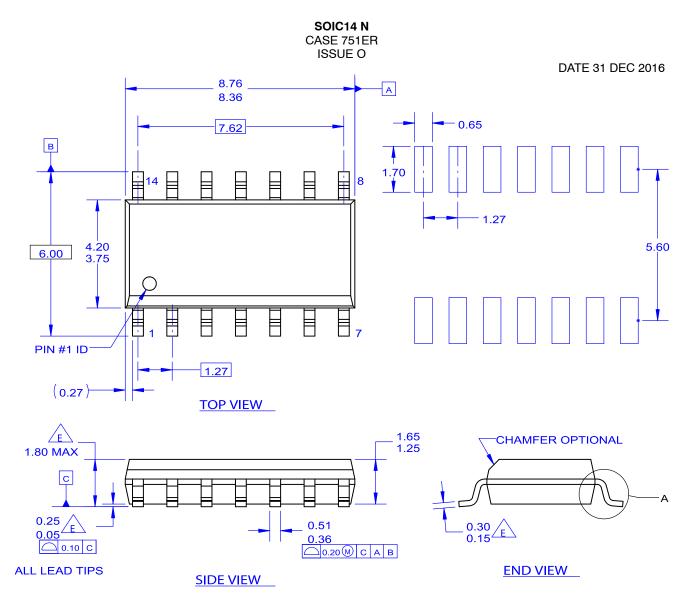
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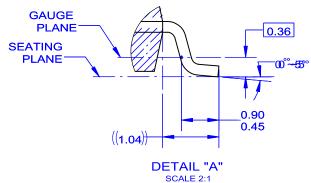
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